

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	90	etch\$3 same (damascene) same ((first and second and third) with (insulat\$3 or dielectric)) same ((first and second and third) with (chemistry or etch\$3)) same (via or hole or contact or "through hole") same (metal or "metal line")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 12:51			
2	BRS	L2	0	1 and @pd<="19960126"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 12:50			
3	BRS	L3	849	(etch\$3 same (damascene)) and (((first and second and third) with (insulat\$3 or dielectric)) same ((first and second and third) with (chemistry or etch\$3)) )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 12:51			
4	BRS	L4	639	((etch\$3 same (damascene)) same (via or hole or contact or "through hole")) and (((first and second and third) with (insulat\$3 or dielectric)) same ((first and second and third) with (chemistry or etch\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 12:50			
5	BRS	L5	0	4 and @pd<="19960126"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 12:53			
6	BRS	L6	825	(etch\$3 same damascene) and ((first and second and third) with (insulat\$3 or dielectric)) same ((first and second and third) with (chemistry or etch\$3)) and (via or hole or contact or "through hole")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 12:52			
7	BRS	L7	0	6 and @pd<="19960126"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:01			
8	BRS	L8	0	"EMA-TAIJI.in. "	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 12:55			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
9	BRS	L9	278	EMA-TAIJI.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 14:12			
10	BRS	L10	11	ANEZAKI-TOHRU.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 14:58			
11	BRS	L11	36	((first and third) with (insulat\$3 or dielectric) with (SiN or Si3N4 or "Si.sub.3N.sub.4")) same ((second and fourth) with (insulat\$3 or dielectric) with (SiO2 or "SiO.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:03			
12	BRS	L12	3	11 and @pd<="19960126"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:05			
13	BRS	L13	35545	(insulat\$3 or dielectric) with ((SiN or Si3N4 or "Si.sub.3N.sub.4" or "silicon nitride") and (SiO2 or "SiO.sub.2" or "silicon dioxide"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:04			
14	BRS	L14	2154	(insulat\$3 or dielectric) with ((SiN or Si3N4 or "Si.sub.3N.sub.4" or "silicon nitride") and (SiO2 or "SiO.sub.2" or "silicon dioxide")) with (known or conventional)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:04			
15	BRS	L15	402	((insulat\$3 or dielectric) with ((SiN or Si3N4 or "Si.sub.3N.sub.4" or "silicon nitride") and (SiO2 or "SiO.sub.2" or "silicon dioxide")) with (known or conventional)) same etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:05			
16	BRS	L16	17	((insulat\$3 or dielectric) with ((SiN or Si3N4 or "Si.sub.3N.sub.4" or "silicon nitride") and (SiO2 or "SiO.sub.2" or "silicon dioxide")) with (known or conventional)) same etch\$3 same (dram or capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:05			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
17	BRS	L17	2	16 and @pd<="19960126"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:07			
18	BRS	L18	71	15 and @pd<="19960126"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:07			
19	BRS	L19	40	18 and "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/12/18 15:07			